

PNP Power Silicon Transistor

Rev. V5

Features

- Available in commercial, JAN, JANTX, JANTXV, JANS and JANSR 100K rads (Si) per MIL-PRF-19500/545
- TO-5 Package: 2N5151L, 2N5153L
- TO-39 (TO-205AD) Package: 2N5151, 2N5153





Electrical Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Breakdown Voltage	$I_{C} = -100 \text{ mA dc}, I_{B} = 0$	V _{(BR)CEO}	V dc	-80	_
Emitter - Base Cutoff Current	$V_{EB} = -4.0 \text{ V dc}, I_{C} = 0$ $V_{EB} = -5.5 \text{ V dc}, I_{C} = 0$	I _{EBO1}	μΑ dc mA dc	_	-1.0 -1.0
Collector - Emitter Cutoff Current	$V_{CE} = -60 \text{ V dc}, V_{BE} = 0$ $V_{CE} = -100 \text{ V dc}, V_{BE} = 0$	I _{CES1}	μΑ dc mA dc	_	-1.0 -1.0
Collector - Emitter Cutoff Current	$V_{CE} = -40 \text{ V dc}, I_{B} = 0$	I _{CEO}	μA dc	_	-50
	V_{CE} = -5.0 V dc, I_{C} = -50 mA dc 2N5151, L 2N5153, L V_{CE} = -5.0 V dc, I_{C} = -2.5 A dc			20 50	
Forward Current Transfer Ratio	2N5151, L 2N5153, L V _{CE} = -5.0 V dc, I _C = -5.0 A dc 2N5151, L 2N5153, L	h _{FE}	-	30 70 20 40	90 200
Collector - Emitter Saturation Voltage	I_C = -2.5 A dc, I_B = -250 mA dc I_C = -5.0 A dc, I_B = -500 mA dc	V _{CE(sat)1}	V dc	_	-0.75 -1.50
Emitter - Base Voltage Non-Saturation	V_{CE} = -5.0 Vdc, I_{C} = -2.5 A dc	V _{BE}	V dc	_	-1.45
Emitter - Base Saturation Voltage	I_{C} = -2.5 A dc, I_{B} = -250 mA dc I_{C} = -5.0 A dc, I_{B} = -500 mA dc	V _{BE(sat)1}	V dc	_	-1.45 -2.20
Collector—Emitter Cutoff Current	T_{C} = +150°C V_{CE} = -60 V dc, V_{BE} = +2 V dc	I _{CEX}	μA dc	_	-25
Forward - Current Transfer Ratio	$T_C = -55^{\circ}C$ $V_{CE} = -5 \text{ V dc}, I_C = -2.5 \text{ A dc}$ 2N5151, L 2N5153, L	h _{FE4}			15 25

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Electrical Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.			
Dynamic Characteristics								
Magnitude of Common Emitter Small-Signal Short-Circuit, Forward-Current Transfer Ratio	V_{CE} = -5.0 V dc, I_{C} = -500 mA dc, f = 10 MHz 2N5151 2N5153	h _{fe}	-	6 7				
Common-Emitter, Small-Signal Short-Circuit, Forward-Current Transfer Ratio $I_C = -100$ mA dc, $V_{CE} = -5.0$ V dc, $f = 1$ kHz 2N5151 2N5153		h _{fe}	-	20 50				
Open-Circuit Output Capacitance	$V_{CB} = -10 \text{ V dc}, I_{E} = 0, f = 1 \text{ MHz}$	C _{obo}	pF	_	250			
Parameter	Test Conditions	Symbol	Units	Min.	Max.			
Switching Characteristics								
Turn-On Time		t _{on}	μs	_	0.5			
Turn-Off Time	$I_C = -5 \text{ A dc}$; $I_{B1} = -500 \text{ mA dc}$, $R_L = 6 \Omega$,	t _{off}	μs	_	1.5			
Storage Time	I_{B2} = -500 mA dc, $V_{BE(off)}$ = -3.7 V dc	ts	μs	_	1.4			
Fall Time		t _f	μs	_	0.5			

Safe Operating Area

DC Tests: $T_C = +25^{\circ}C$, I Cycle, $t_p = 1 \text{ s}$

Test 1: $V_{CE} = -5 \text{ V dc}, I_{C} = -2 \text{ A dc}$ Test 2: $V_{CE} = -32 \text{ V dc}, I_{C} = -310 \text{ mA dc}$ Test 3: $V_{CE} = -80 \text{ V dc}, I_{C} = -12.5 \text{ mA dc}$



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Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Ratings	Symbol	Value
Collector - Emitter Voltage	V _{CEO}	-80 V dc
Collector - Base Voltage	V _{CBO}	-100 V dc
Emitter - Base Voltage	V _{EBO}	-5.5 V dc
Collector Current	Ic	-2 A dc -10 A dc ⁽³⁾
Reverse Pulse Energy (4)		15 mj
Total Power Dissipation $^{(1)}$ @ $T_A = +25^{\circ}C$ @ $T_C = +25^{\circ}C$	P _T	1 W 10 W
Operating & Storage Temperature Range	T _J , T _{STG}	-65°C to +200°C

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case	R _{θJC} (2)	10°C/W
Thermal Resistance, Junction to Ambient	R _{0JA} (2)	175°C/W

⁽¹⁾ See figures 6, 7, 8 and 9 of MIL-PRF-19500/545 for temperature-power derating curves.

⁽²⁾ See figures 10, 11 and 12 of MIL-PRF-19500/545 for transient thermal impedance graph.

⁽³⁾ This value applies for $P_W \le 8.3$ ms, duty cycle ≤ 1 percent.

⁽⁴⁾ This rating is based on the capability of the transistors to operate safely in the unclamped inductive load energy test circuit, see subgroup 5 of the group A inspection table and figure 13 of MIL-PRF-19500/545.

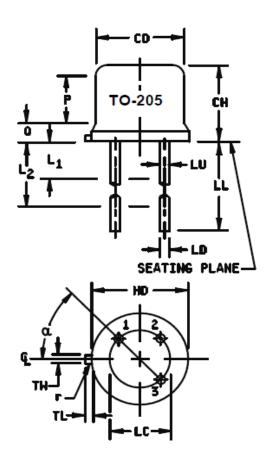


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Outline Drawings (TO-5, TO-39)

	Dimensions				
Symbol		Inches		Millimeters	
	Min	Max	Min	Max	
CD	.305	.335	7.75	8.51	6
СН	.240	.260	6.10	6.60	
HD	.335	.370	8.51	9.40	
LC	.200	.200 TP		5.08 TP	
LD	.016	.021	0.41	0.53	8, 9
LL	s	See notes 8, 9, 12, 13			
LU	.016	.019	0.41	0.48	8, 9
L ₁		.050		1.27	8, 9
L ₂	.250		6.35		8, 9
Q		.050		1.27	6
TL	.029	.045	0.74	1.14	4, 5
TW	.028	.034	0.71	0.86	3
г		.010		0.25	11
α	45°	45° TP		45° TP	
Р	.100		2.54		



NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 inch (0.28 mm).
- 4. TL measured from maximum HD.
- 5. Outline in this zone is not controlled.
- 6. CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
- 8. LU applied between L₁ and L₂. LD applies between L₂ and LL minimum. Diameter is uncontrolled in L₁ and beyond LL minimum.
- 9. All three leads.
- The collector shall be electrically and mechanically connected to the case.
- 11. r (radius) applies to both inside corners of tab.
- 12. In accordance with ASME Y14.5M, diameters are equivalent to \$\psi\$x symbology.
- 13. For transistor types 2N5151 and 2N5153, LL is .5 inch (13 mm) minimum, and .75 inch (19 mm) maximum.
- For transistor types 2N5151L and 2N5153L, LL is 1.5 inch (38 mm) minimum and 1.75 inch (44.4 mm) maximum.
- Lead designation, depending on device type, shall be as follows: lead numbering; lead 1 = emitter, lead 2 = base, and lead 3 = collector.

FIGURE 1. Physical dimensions (TO-205).



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